

NPN RF TRANSISTOR

DESCRIPTION:

The **ASI MSC80183** is a Silicon NPN Microwave Transistor Supplied in a Common Base Package, Designed for Amplifier/Oscillator Applications up to 2.3 GHz.

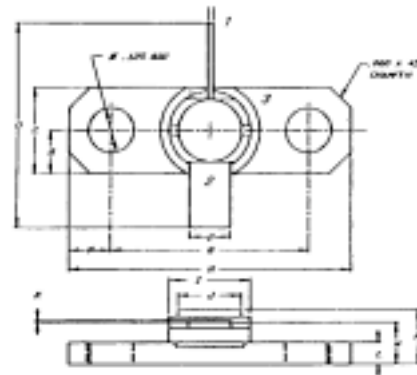
FEATURES:

- Hermetically Sealed Package
- Gold Metallization

MAXIMUM RATINGS

I_C	1.2 A
V_{CC}	26 V
V_{EB}	3.5 V
P_{DISS}	21.4 W @ $T_C = 50^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$
θ_{JC}	$7.0^\circ C/W$

PACKAGE 230 2L FLG		
	Minimum Inches/mm	Maximum Inches/mm
A	.025/0.64	.035/0.89
B	.115/2.92 BSC	
C	.225/5.72	.235/5.97
D	.720/18.29	.750/19.05
E	.110/2.79	.120/3.05
F	.120/3.05 BSC	
G	.555/14.10	.565/14.35
H	.795/20.19	.805/20.45
I	.222/5.64	.236/5.99
J	.165/4.19	.180/4.57
K	.002/0.05	.007/0.18
L	.055/1.40	.067/1.70
M	.120/3.18	.140/3.56
N		.170/4.32



1 = Collector 2 = Emitter
3 = Base

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CER}	$I_C = 5.0$ mA $R_{BE} = 10\Omega$	44			V
BV_{CBO}	$I_C = 1.0$ mA	44			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CBO}	$V_{CB} = 22$ V			0.5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	30		300	
C_{OB}	$V_{CB} = 22$ V $f = 1.0$ MHz			8.5	pF
P_{out}	$V_{CC} = 22$ V $P_{IN} = 0.76$ W $f = 2.3$ GHz	7.0	8.0		W
P_G		9.6	10.2		Db
η_C		40	45		%



ADVANCED SEMICONDUCTOR, INC.

7525 ETHEL AVENUE • NORTH HOLLYWOOD, CA 91605 • (818) 982-1202 • TELEX: 18-2651 • FAX (818) 765-3004